

ABSTRACT OF THE DISCLOSURE

A semiconductor device may include a substrate and an insulating layer formed on the substrate. A first device may be formed on the insulating layer, including a first fin. The first fin may be formed on the insulating layer and may have a first fin aspect ratio. A second device may be formed on the insulating layer, including a second fin. The second fin may be formed on the insulating layer and may have a second fin aspect ratio different from the first fin aspect ratio.